3.3V CMOS 20-BIT BUS-INTERFACE D-TYPE LATCH WITH 3-STATE OUTPUTS

IDT74ALVC16841

FEATURES:

- **0.5 MICRON CMOS Technology**
- **Typical $t_{SK(o)}$ (Output Skew) < 250ps**
- **ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)**
- **Vcc = 3.3V ± 0.3V, Normal Range**
- **Vcc = 2.7V to 3.6V, Extended Range**
- **Vcc = 2.5V ± 0.2V**
- **CMOS power levels (0.4µ W typ. static)**
- **Rail-to-Rail output swing for increased noise margin**
- **Available in SSOP, TSSOP, and TVSOP packages**

DRIVE FEATURES:

- **High Output Drivers: ±24mA**
- **Suitable for heavy loads**

APPLICATIONS:

- **3.3V high speed systems**
- **3.3V and lower voltage computing systems**

DESCRIPTION:

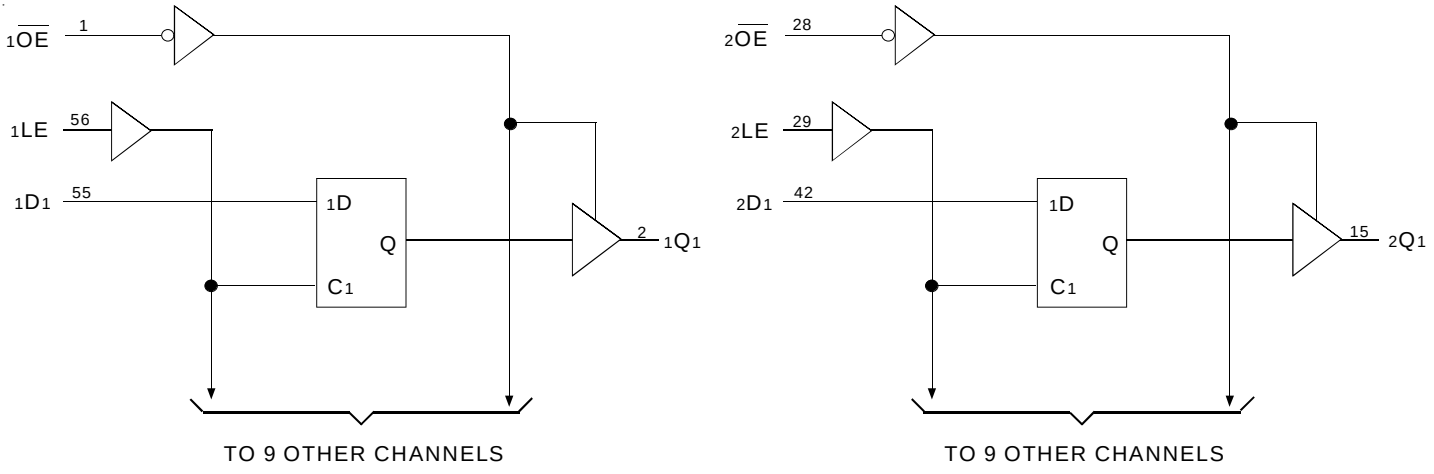
This 20-bit bus-interface D-type latch is built using advanced dual metal CMOS technology. The ALVC16841 features 3-state outputs designed specifically for driving highly capacitive relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, unidirectional bus drivers, and working registers.

The ALVC16841 can be used as two 10-bit latches or one 20-bit latch. The 20 latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs. While the latch-enable (1LE or 2LE) input is high, the Q outputs of the corresponding 10-bit latch follow the D inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

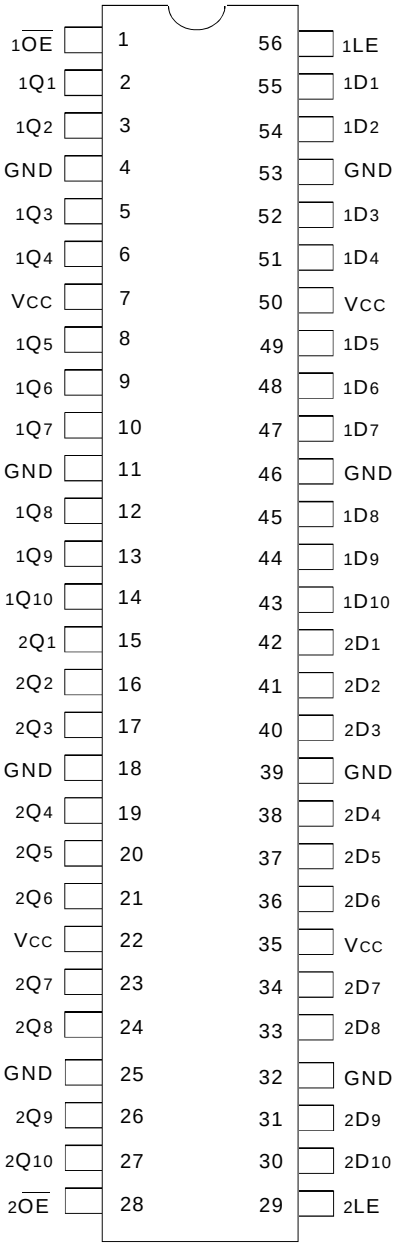
A buffered output-enable ($\overline{1OE}$ or $\overline{2OE}$) input can be used to place the outputs of the corresponding 10-bit latch in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. $\overline{OE}$ does not affect the internal operation of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The ALVC16841 has been designed with a ±24mA output driver. This driver is capable of driving a moderate to heavy load while maintaining speed performance.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



SSOP/ TSSOP/ TVSOP
TOP VIEW

PIN DESCRIPTION

Pin Names	Description
xDx	Data Inputs
LE	Latch Enable Input (Active HIGH)
$\overline{xOE}$	Output Enable Input (Active LOW)
xQx	3-State Outputs

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Description	Max	Unit
V_{TERM}(2)	Terminal Voltage with Respect to GND	–0.5 to +4.6	V
V_{TERM}(3)	Terminal Voltage with Respect to GND	–0.5 to V_{CC}+0.5	V
T_{STG}	Storage Temperature	–65 to +150	°C
I_{OUT}	DC Output Current	–50 to +50	mA
I_{IK}	Continuous Clamp Current, $V_I < 0$ or $V_I > V_{CC}$	±50	mA
I_{OK}	Continuous Clamp Current, $V_O < 0$	–50	mA
I_{CC} I_{SS}	Continuous Current through each V_{CC} or GND	±100	mA

NOTES:
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. V_{CC} terminals.
3. All terminals except V_{CC}.

CAPACITANCE (T_A = +25°C, F = 1.0MHz)

Symbol	Parameter(1)	Conditions	Typ.	Max.	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V	5	7	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V	7	9	pF
C_{OUT}	I/O Port Capacitance	V_{IN} = 0V	7	9	pF

NOTE:
1. As applicable to the device type.

FUNCTION TABLE (EACH 10-BIT LATCH)(1)

Inputs			Outputs
xDx	xLE	$\overline{xOE}$	xQx
H	H	L	H
L	H	L	L
X	L	L	Q_0(2)
X	X	H	Z

NOTES:
1. H = HIGH Voltage Level
   L = LOW Voltage Level
   X = Don't Care
   Z = High Impedance
   ↑ = LOW-to-HIGH transition
2. Output level before the indicated steady-state input conditions were established.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:
Operating Condition: T_A = –40°C to +85°C

Symbol	Parameter	Test Conditions		Min.	Typ.(1)	Max.	Unit
V_{IH}	Input HIGH Voltage Level	V_{CC} = 2.3V to 2.7V		1.7	—	—	V
		V_{CC} = 2.7V to 3.6V		2	—	—	
V_{IL}	Input LOW Voltage Level	V_{CC} = 2.3V to 2.7V		—	—	0.7	V
		V_{CC} = 2.7V to 3.6V		—	—	0.8	
I_{IH}	Input HIGH Current	V_{CC} = 3.6V	V_I = V_{CC}	—	—	±5	µA
I_{IL}	Input LOW Current	V_{CC} = 3.6V	V_I = GND	—	—	±5	µA
I_{OZH}	High Impedance Output Current	V_{CC} = 3.6V	V_O = V_{CC}	—	—	±10	µA
I_{OZL}	(3-State Output pins)		V_O = GND	—	—	±10	
V_{IK}	Clamp Diode Voltage	V_{CC} = 2.3V, I_{IN} = –18mA		—	–0.7	–1.2	V
V_H	Input Hysteresis	V_{CC} = 3.3V		—	100	—	mV
I_{CCL} I_{CCH} I_{CCZ}	Quiescent Power Supply Current	V_{CC} = 3.6V V_{IN} = GND or V_{CC}		—	0.1	40	µA
ΔI_{CC}	Quiescent Power Supply Current Variation	One input at V_{CC} - 0.6V, other inputs at V_{CC} or GND		—	—	750	µA

NOTE:
1. Typical values are at V_{CC} = 3.3V, +25°C ambient.

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions(1)		Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = 2.3V to 3.6V	I_{OH} = – 0.1mA	V_{CC} – 0.2	—	V
		V_{CC} = 2.3V	I_{OH} = – 6mA	2	—	
		V_{CC} = 2.3V	I_{OH} = – 12mA	1.7	—	
		V_{CC} = 2.7V		2.2	—	
		V_{CC} = 3V		2.4	—	
		V_{CC} = 3V	I_{OH} = – 24mA	2	—	
V_{OL}	Output LOW Voltage	V_{CC} = 2.3V to 3.6V	I_{OL} = 0.1mA	—	0.2	V
		V_{CC} = 2.3V	I_{OL} = 6mA	—	0.4	
			I_{OL} = 12mA	—	0.7	
		V_{CC} = 2.7V	I_{OL} = 12mA	—	0.4	
		V_{CC} = 3V	I_{OL} = 24mA	—	0.55	

NOTE:
1. V_{IH} and V_{IL} must be within the min. or max. range shown in the DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE table for the appropriate V_{CC} range. T_A = – 40°C to + 85°C.

OPERATING CHARACTERISTICS, T_A = 25°C

Symbol	Parameter	Test Conditions	V_{CC} = 2.5V ± 0.2V	V_{CC} = 3.3V ± 0.3V	Unit
			Typical	Typical	
C_{PD}	Power Dissipation Capacitance Outputs enabled	C_L = 0pF, f = 10Mhz	12	20	pF
C_{PD}	Power Dissipation Capacitance Outputs disabled		1	3	

SWITCHING CHARACTERISTICS(1)

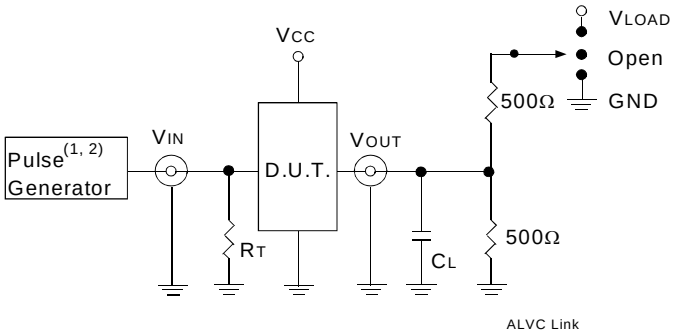
Symbol	Parameter	V_{CC} = 2.5V ± 0.2V		V_{CC} = 2.7V		V_{CC} = 3.3V ± 0.3V		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay xDx to xQx	1	5	—	4.7	1.2	3.9	ns
t_{PLH} t_{PHL}	Propagation Delay LE to xQx	1	5.6	—	5.1	1	4.3	ns
t_{PZH} t_{PZL}	Output Enable Time $\overline{xOE}$ to xQx	1	6.2	—	6	1	4.9	ns
t_{PHZ} t_{PLZ}	Output Disable Time $\overline{xOE}$ to xQx	1.1	5.3	—	4.3	1.3	4.1	ns
t_{SU}	Set-up Time, data before LE↑	0.9	—	0.7	—	1.1	—	ns
t_H	Hold Time, data after LE↑	1.2	—	1.5	—	1.1	—	ns
t_W	Pulse Duration, LE HIGH or LOW	3.3	—	3.3	—	3.3	—	ns
$t_{SK(O)}$	Output Skew(2)	—	—	—	—	—	500	ps

NOTES:
1. See TEST CIRCUITS AND WAVEFORMS. T_A = – 40°C to + 85°C.
2. Skew between any two outputs of the same package and switching in the same direction.

TEST CIRCUITS AND WAVEFORMS

TEST CONDITIONS

Symbol	$V_{CC}^{(1)}$=3.3V±0.3V	$V_{CC}^{(1)}$=2.7V	$V_{CC}^{(2)}$=2.5V±0.2V	Unit
V_{LOAD}	6	6	2 x Vcc	V
V_{IH}	2.7	2.7	Vcc	V
V_T	1.5	1.5	Vcc / 2	V
V_{LZ}	300	300	150	mV
V_{HZ}	300	300	150	mV
C_L	50	50	30	pF



Test Circuit for All Outputs

DEFINITIONS:

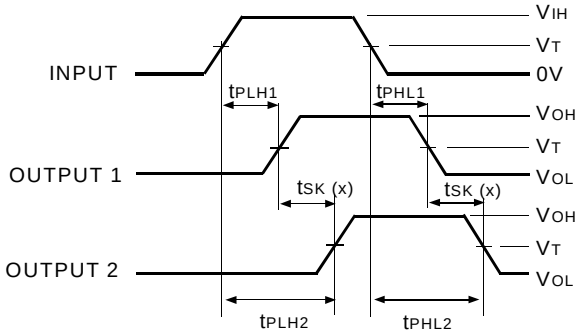
C_L = Load capacitance: includes jig and probe capacitance.
R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

NOTES:

1. Pulse Generator for All Pulses: Rate ≤ 1.0MHz; t_F ≤ 2.5ns; t_R ≤ 2.5ns.
2. Pulse Generator for All Pulses: Rate ≤ 1.0MHz; t_F ≤ 2ns; t_R ≤ 2ns.

SWITCH POSITION

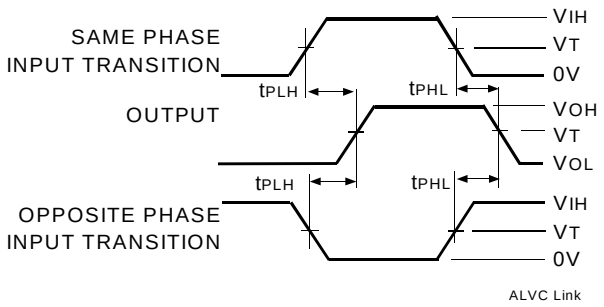
Test	Switch
Open Drain Disable Low Enable Low	V_{LOAD}
Disable High Enable High	GND
All Other Tests	Open



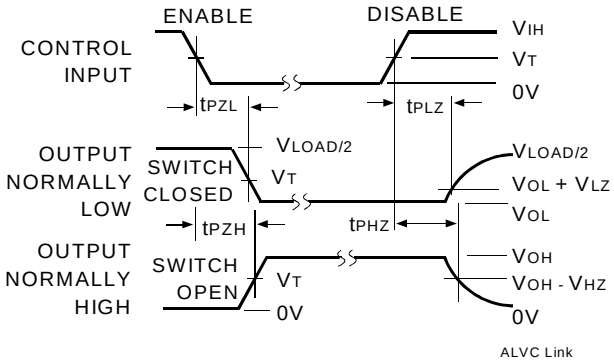
Output Skew - $t_{SK}(x)$

NOTES:

1. For t_{SK}(o) OUTPUT1 and OUTPUT2 are any two outputs.
2. For t_{SK}(b) OUTPUT1 and OUTPUT2 are in the same bank.



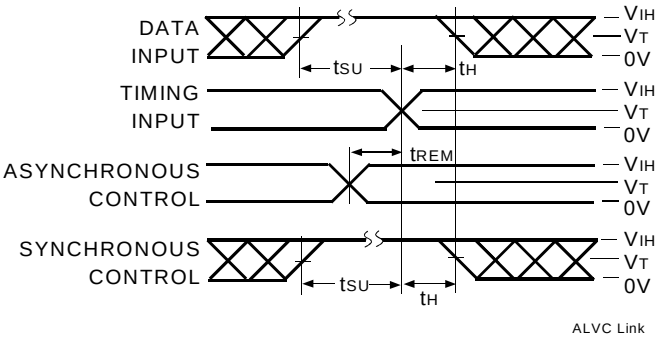
Propagation Delay



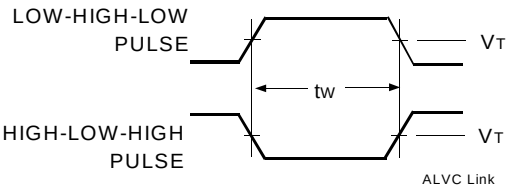
Enable and Disable Times

NOTE:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.

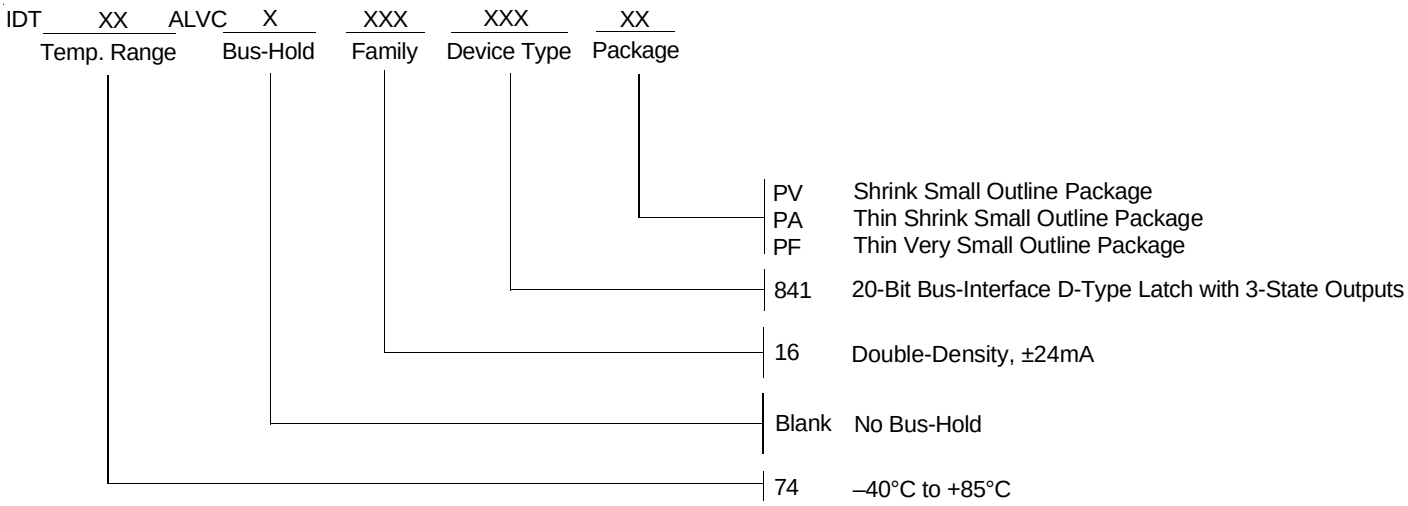


Set-up, Hold, and Release Times



Pulse Width

ORDERING INFORMATION



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